

Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Code.	Min.	Typ.	Max.	Units	Test Conditions
V _{BR CEO}	Collector-to-Emitter Breakdown Voltage		30			V	I _C =100uA E _e =0mW/c
V _{BR ECO}	Emitter-to-Collector Breakdown Voltage		5			V	I _E =100uA E _e =0mW/c
V _{CE (SAT)}	Collector-to-Emitter Saturation Voltage				0.8	V	I _C =2mA E _e =20mW/c
I _{CEO}	Collector Dark Current				100	nA	V _{CE} =10V E _e =0mW/c
T _R	Rise Time (10 to 90)			15		us	V _{CE} = 5V I _C =1mA R _L =1000Ω
T _F	Fall Time (90 to 10)			15		us	
I _(ON)	On State Collector Current	H	0.3		0.6	mA	V _{CE} = 5V E _e =1mW/c λ=940nm
		I	0.4		1		
		K	0.7		1.5		

Absolute Maximum Ratings at TA=25°C

Parameter	Max.Ratings
Collector-to-Emitter Voltage	30V
Emitter-to-Collector Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature	-40°C To +85°C
Storage Temperature	-40°C To +85°C
Lead Soldering Temperature (>5mm for 5sec)	260°C

RELATIVE SPECTRAL RESPONSE

